

Product Summary

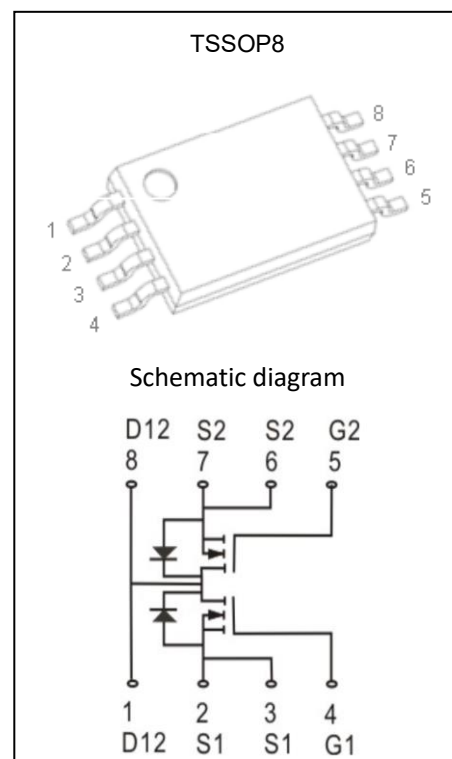
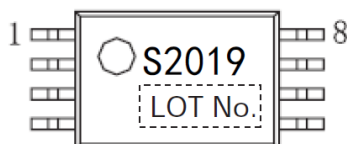
$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
20V	17m Ω @4.5V	5A
	22m Ω @2.5V	

Feature

- Trench Technology Power MOSFET
- Excellent $R_{DS(ON)}$
- Low Gate Charge
- High Power and Current Handling Capability
- Surface Mount Package

Application

- Battery Protection
- Load Switch
- Power Management

MARKING:

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 10	V
Continuous Drain Current ^{1,5}	I_D	5	A
Pulsed Drain Current ²	I_{DM}	25	A
Power Dissipation ^{4,5}	P_D	2	W
Thermal Resistance from Junction to Ambient ⁵	$R_{\theta JA}$	62.5	$^{\circ}\text{C/W}$
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55~ +150	$^{\circ}\text{C}$
Lead Temperature for Soldering Purposes(1/8" from case for 10s)	T_L	260	$^{\circ}\text{C}$

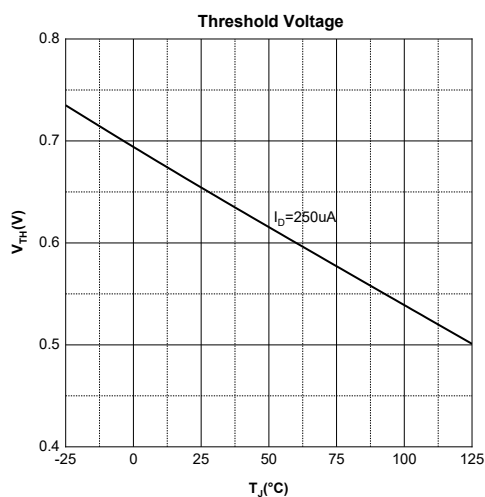
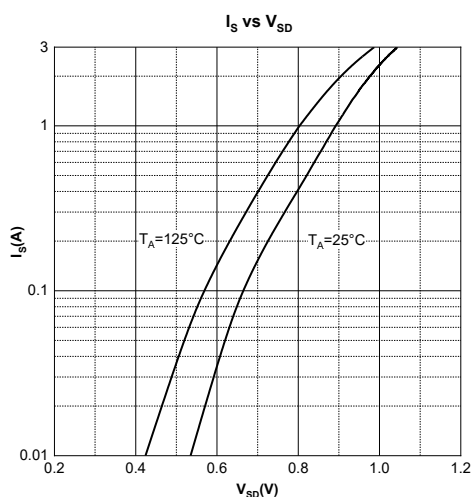
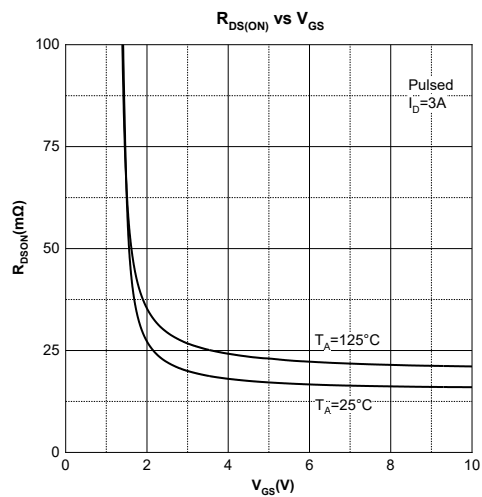
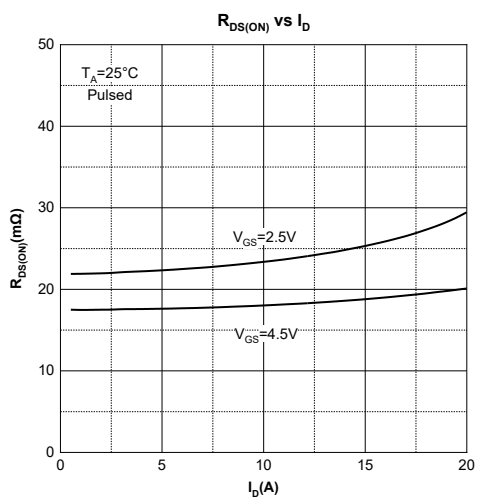
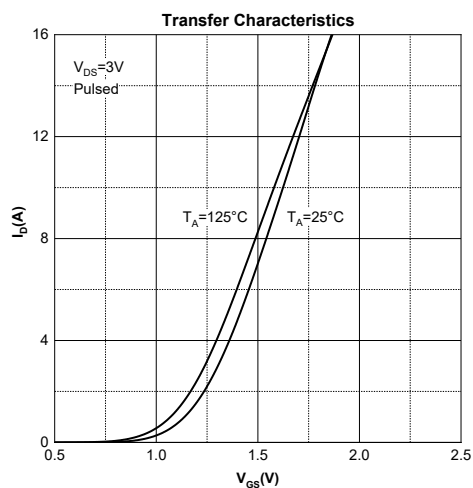
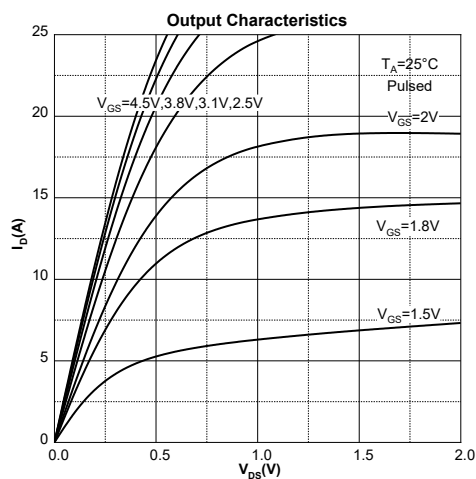
MOSFET ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

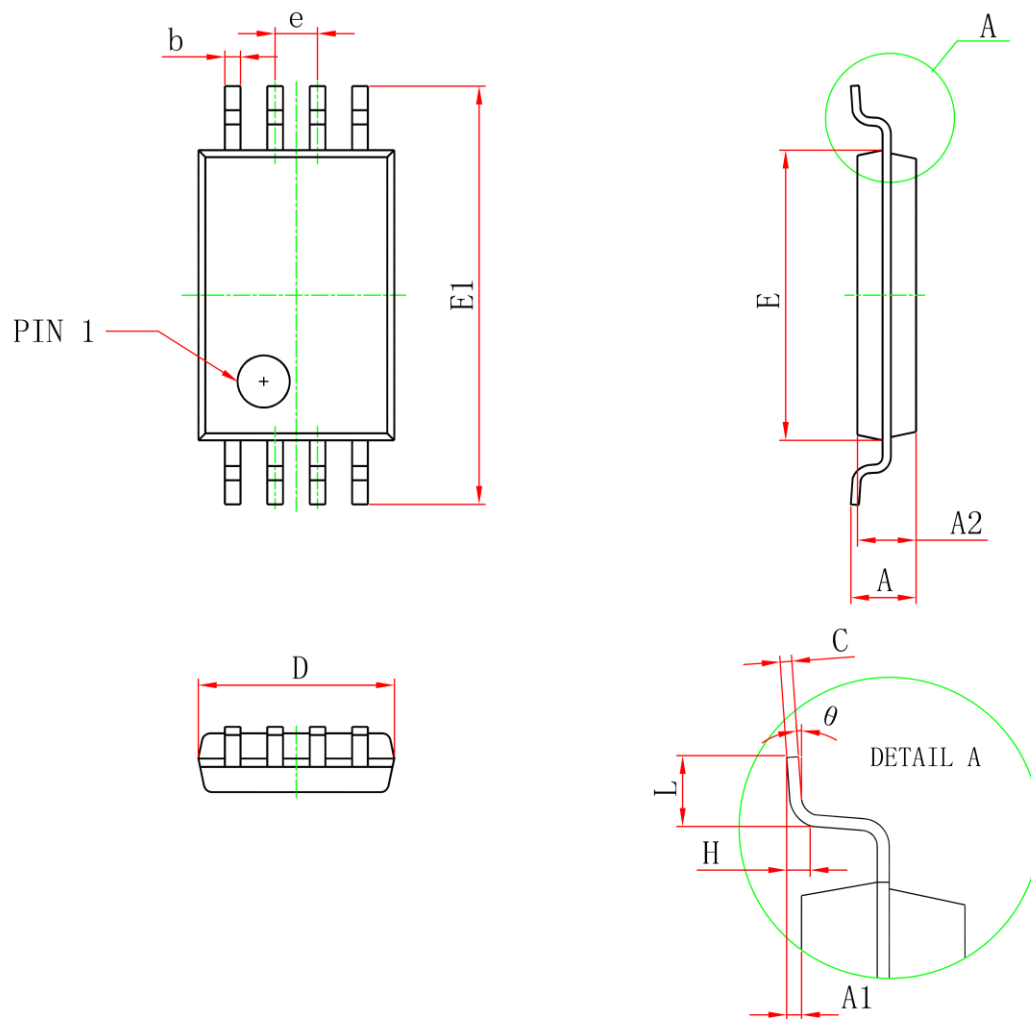
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	20			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 18V, V _{GS} = 0V			1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} = ±10V, V _{DS} = 0V			±100	nA
On Characteristics ³						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	0.45	0.7	1.2	V
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} = 4.5V, I _D = 3A		17	27	mΩ
		V _{GS} = 2.5V, I _D = 3A		22	35	
Forward Tranconductance	g _{FS}	V _{DS} = 5V, I _D = 4.5A	5			S
Dynamic Characteristics ⁴						
Input Capacitance	C _{iss}	V _{DS} = 10V, V _{GS} = 0V, f = 1MHz		436		pF
Output Capacitance	C _{oss}			59		
Reverse Transfer Capacitance	C _{rss}			52		
Gate Resistance	R _g	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz		2.8		Ω
Switching Characteristics ⁴						
Total Gate Charge	Q _g	V _{DS} = 10V, V _{GS} = 4.5V, I _D = 3A		6.2		nC
Gate-Source Charge	Q _{gs}			0.6		
Gate-Drain Charge	Q _{gd}			2.0		
Turn-On Delay Time	t _{d(on)}	V _{DD} = 10V, V _{GS} = 4V, I _D = 1A, R _G = 10Ω		18		ns
Turn-On Rise Time	t _r			5		
Turn-Off Delay Time	t _{d(off)}			43		
Turn-Off Fall Time	t _f			20		
Source-Drain Diode Characteristics						
Diode Forward Voltage ³	V _{SD}	V _{GS} = 0V, I _S = 1.2A			1.2	V

Notes :

- 1.The maximum current rating is limited by package.
- 2.Pulse Test : Pulse Width ≤ 10μs, duty cycle ≤ 1%.
- 3.Pulse Test : Pulse Width ≤ 300μs, duty cycle ≤ 2%.
- 4.The power dissipation P_D is limited by T_{J(MAX)} = 150°C.
- 5.Device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A = 25°C.

Typical Characteristics



TSSOP8 Package Information


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
D	2.800	3.100	0.110	0.122
E	4.300	4.500	0.169	0.177
b	0.200	0.300	0.008	0.012
c	0.090	0.200	0.004	0.008
E1	6.200	6.600	0.244	0.260
A	1.200MAX		0.047MAX	
A2	0.800	1.050	0.031	0.041
A1	0.050	0.150	0.002	0.006
e	0.650BSC		0.026TYP	
L	0.450	0.750	0.018	0.030
H	0.250TYP		0.010TYP	
θ	1°	7°	1°	7°

Attention:

- GreenPower Electronics reserves the right to improve product design function and reliability without notice.
- Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.
- GreenPower Electronics products belong to consumer electronics or other civilian electronic products.